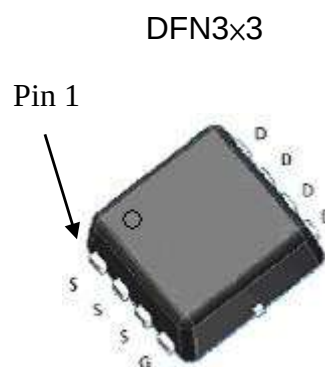


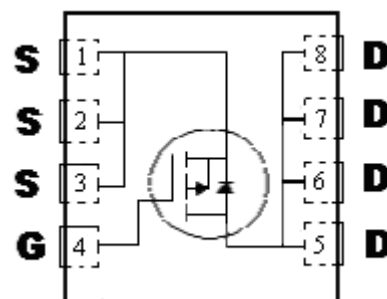
P-Channel Enhancement Mode Power MOSFET

Features:

- Simple drive requirement
- Low on-resistance
- Fast switching speed
- Pb-free lead plating and halogen-free package



BV _{DSS}	-150V
I _D	-4.5A @ V _{GS} =-10V, T _C =25°C
R _{DS(on)(Typ)}	0.78Ω @ V _{GS} =-10V, I _D =-1.5A



G : Gate S : Source D : Drain

Ordering Information

Device	Package	Shipping
KSPRE800P15	DFN3x3 (Pb-free lead plating and halogen-free package)	3000 pcs / tape & reel

Absolute Maximum Ratings (T_C=25°C, unless otherwise noted)

Parameter		Symbol	Limits	Unit
Drain-Source Voltage		V _{DS}	-150	V
Gate-Source Voltage		V _{GS}	±30	
Continuous Drain Current @ T _C =25°C, V _{GS} =-10V		I _D	-4.5	A
Continuous Drain Current @ T _C =100°C, V _{GS} =-10V			-2.8	
Continuous Drain Current @ T _A =25°C, V _{GS} =-10V *3			-1.0	
Continuous Drain Current @ T _A =70°C, V _{GS} =-10V *3			-0.8	
Pulsed Drain Current *1, 2		I _{DM}	-12	
Continuous Source-Drain Diode Current	T _C =25°C	I _S	-4.5	
Avalanche Current		I _{AS}	-12	
Avalanche Energy @ L=0.1mH, I _D =-12A, V _{GS} =-10V *4		E _{AS}	7.2	mJ
Maximum Power Dissipation	T _C =25°C	P _D	42	W
	T _C =70°C		27	
	T _A =25°C *3		2.1	
	T _A =70°C *3		1.3	
Operating Junction and Storage Temperature Range		T _j , T _{stg}	-55~+150	°C

Thermal Data

Parameter	Symbol	Typ	Maximum	Unit
Thermal Resistance, Junction-to-ambient *3	R _{th,j-a}	50	60	°C/W
Thermal Resistance, Junction-to-case	R _{th,j-c}	2.5	3	

- Note : 1. Pulse width limited by maximum junction temperature.
2. Duty cycle ≤ 1%.
3. Surface mounted on 1 in² copper pad of FR-4 board; 135°C/W when mounted on minimum pad of 2 oz. copper.
4. 100% tested by conditions of L=0.1mH, V_{GS}=-10V, I_{AS}=-4A, V_{DD}=-25V

Characteristics (T_C=25°C, unless otherwise specified)

Symbol	Min.	Typ.	Max.	Unit	Test Conditions
Static					
BV _{DSS}	-150	-	-	V	V _{GS} =0V, I _D =-250μA
ΔBV _{DSS} /ΔT _J	-	-150	-	mV/°C	I _D =-250μA, reference to 25°C
ΔV _{GS(th)} /ΔT _J	-	6	-		
V _{GS(th)}	-2	-	-4	V	V _{DS} = V _{GS} , I _D =-250μA
I _{GSS}	-	-	±100	nA	V _{GS} =±20V, V _{DS} =0V
I _{DSS}	-	-	-1	μA	V _{DS} = -120V, V _{GS} = 0V
	-	-	-10		V _{DS} = -120V, V _{GS} = 0V, T _J =85°C
R _{DS(ON)} *1	-	0.78	1.2	Ω	V _{GS} = -10V, I _D =-1.5A
G _{FS} *1	-	3.2	-	S	V _{DS} = -10V, I _D =-3A

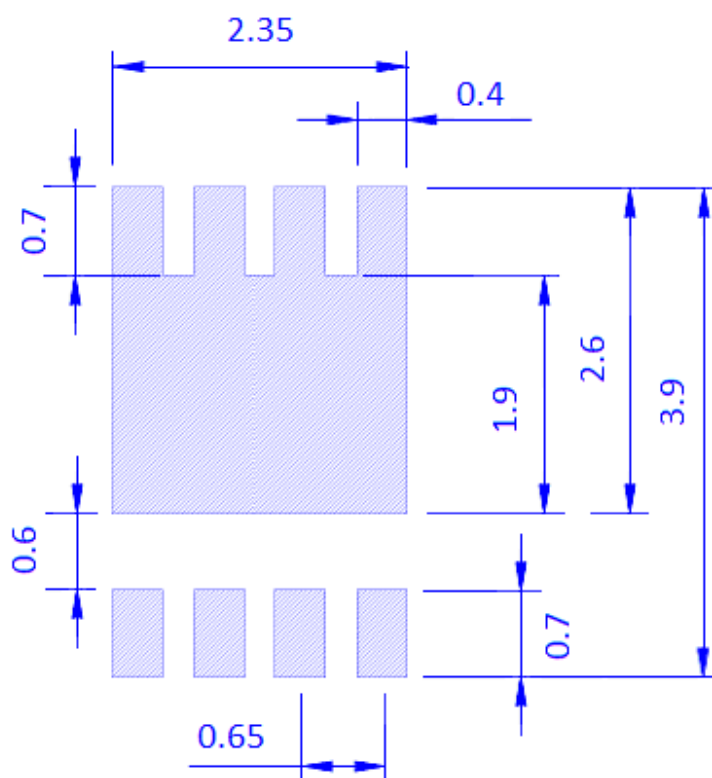
Dynamic					
Qg *1, 2	-	6.8	-	nC	V _{DS} =-75V, I _D =-3A, V _{GS} =-10V
Qgs *1, 2	-	1.7	-		
Qgd *1, 2	-	1.9	-		
t _{d(ON)} *1, 2	-	7.2	-	ns	V _{DS} =-75V, I _D =-3A, V _{GS} =-10V, R _G =25Ω
t _r *1, 2	-	17.4	-		
t _{d(OFF)} *1, 2	-	17	-		
t _f *1, 2	-	14.6	-		
C _{iss}	-	304	-	pF	V _{DS} =-25V, V _{GS} =0V, f=1MHz
C _{oss}	-	30	-		
C _{rss}	-	27	-		
R _g	-	5.7	-	Ω	f=1MHz
Source-Drain Diode					
I _S *1	-	-	-4.5	A	T _C =25°C
I _{SM} *3	-	-	-12		
V _{SD} *1	-	-0.87	-1.3	V	I _F =-3A, V _{GS} =0V
t _{rr}	-	38.6	-	ns	I _F =-3A, dI _F /dt=100A/μs
Q _{rr}	-	67.3	-	nC	

Note : *1.Pulse Test : Pulse Width ≤300μs, Duty Cycle≤2%

*2.Independent of operating temperature

*3.Pulse width limited by maximum junction temperature.

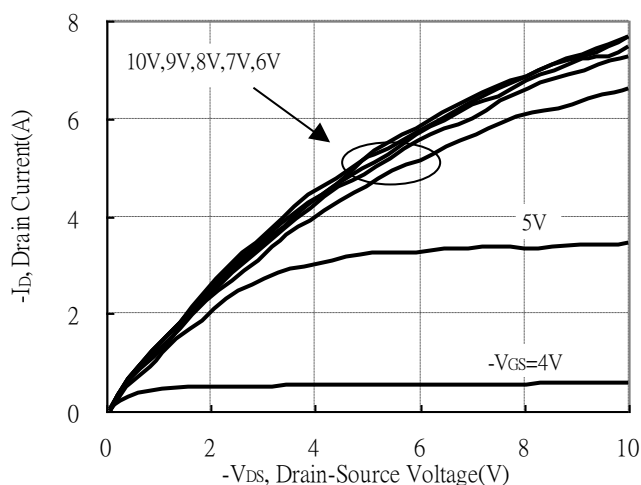
Recommended Soldering Footprint



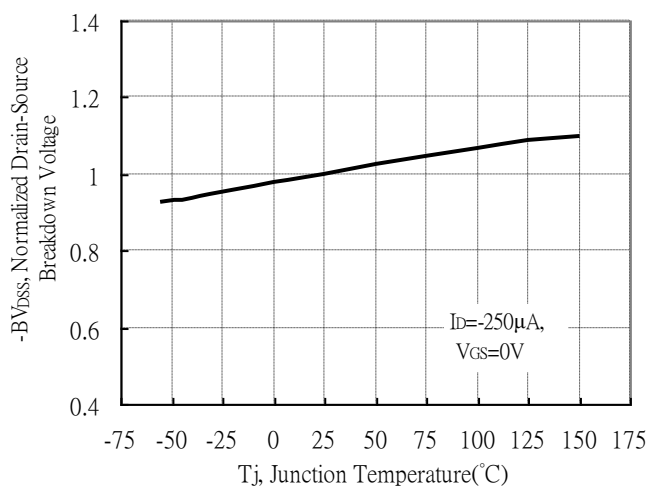
unit : mm

Typical Characteristics

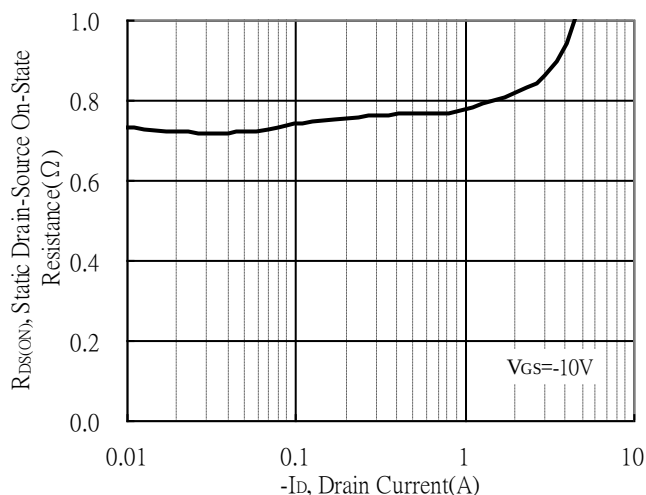
Typical Output Characteristics



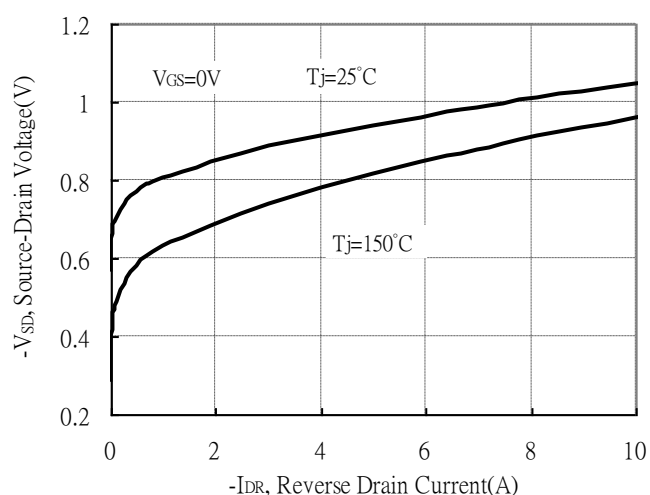
Breakdown Voltage vs Ambient Temperature



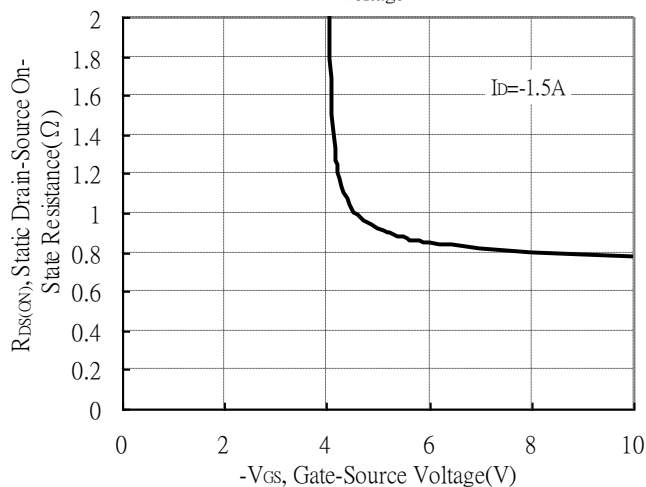
Static Drain-Source On-State resistance vs Drain Current



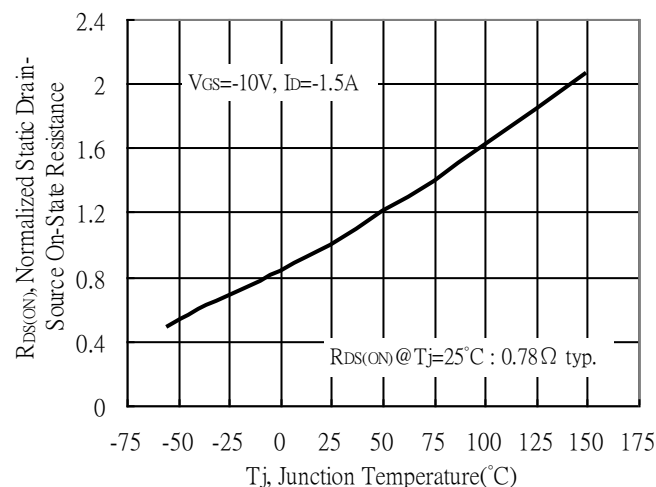
Reverse Drain Current vs Source-Drain Voltage



Static Drain-Source On-State Resistance vs Gate-Source Voltage

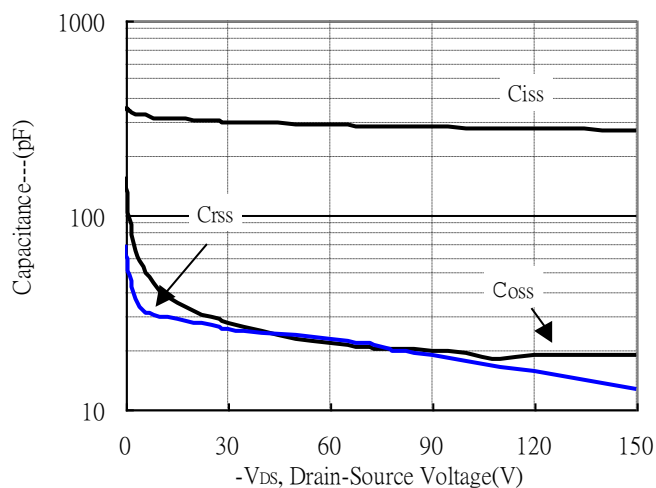


Drain-Source On-State Resistance vs Junction Temperature

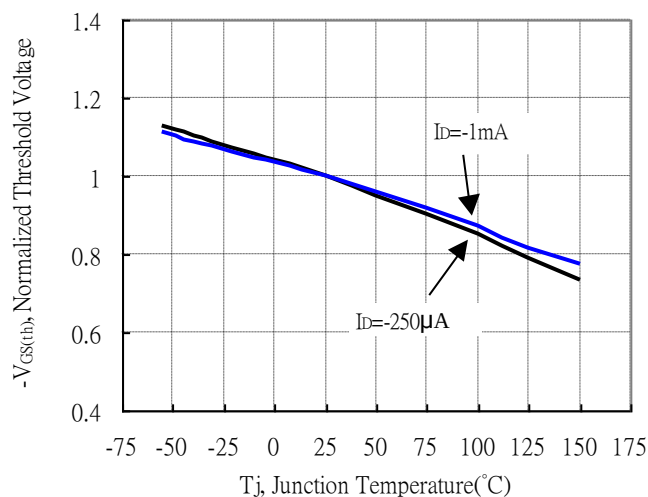


Typical Characteristics(Cont.)

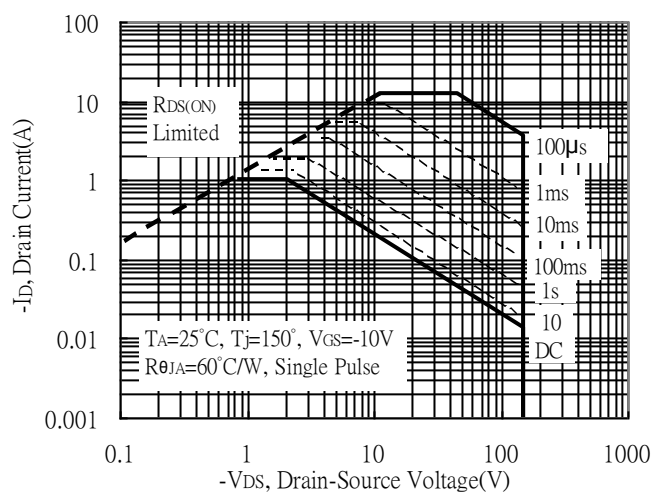
Capacitance vs Drain-to-Source Voltage



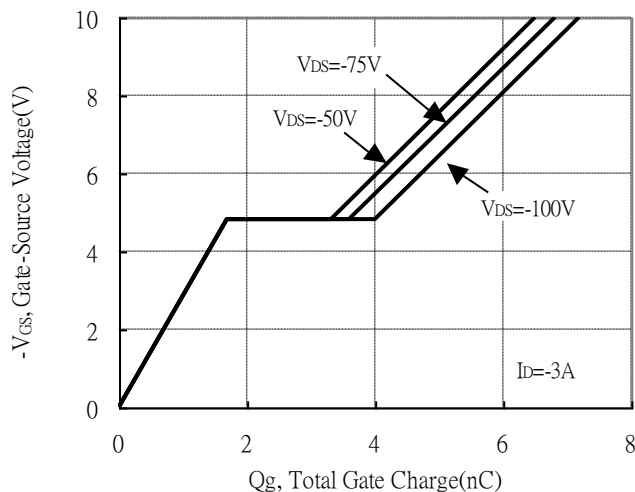
Threshold Voltage vs Junction Temperature



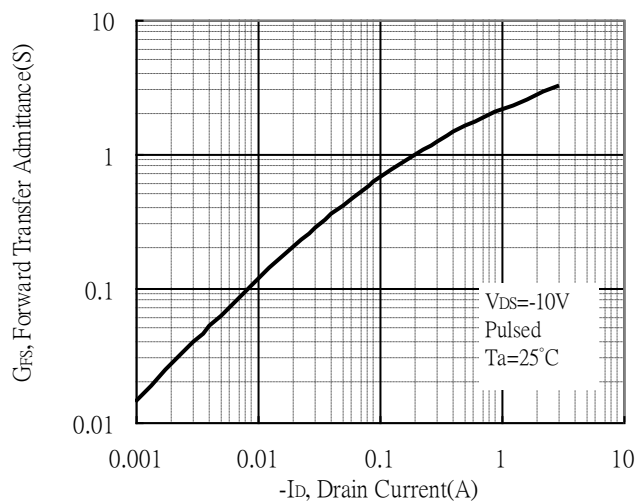
Maximum Safe Operating Area



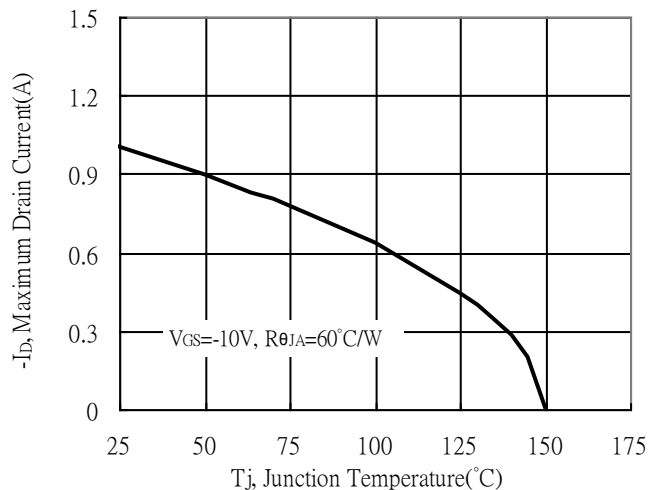
Gate Charge Characteristics



Forward Transfer Admittance vs Drain Current

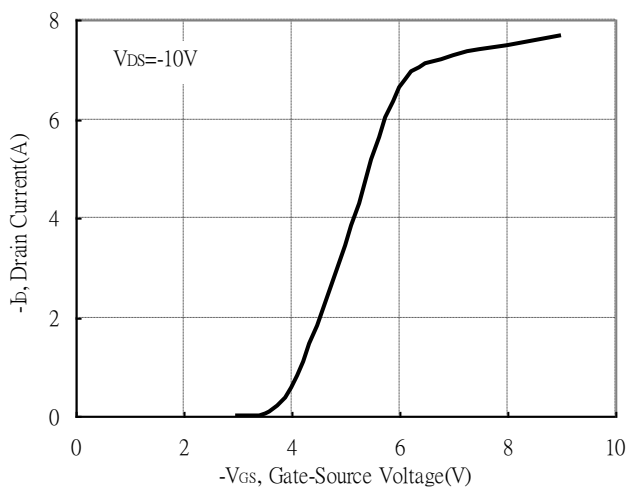


Maximum Drain Current vs Junction Temperature

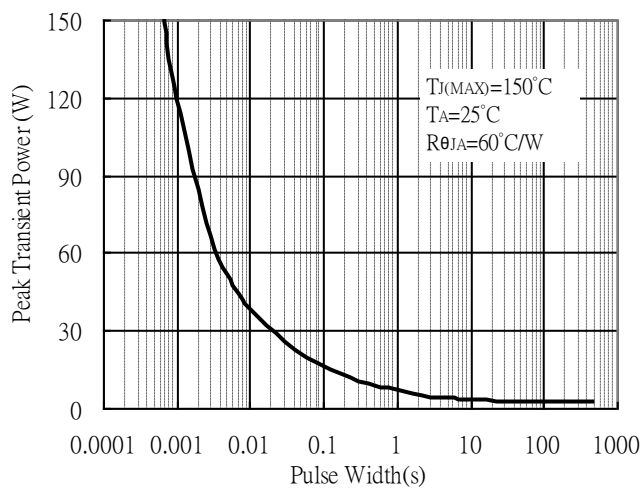


Typical Characteristics(Cont.)

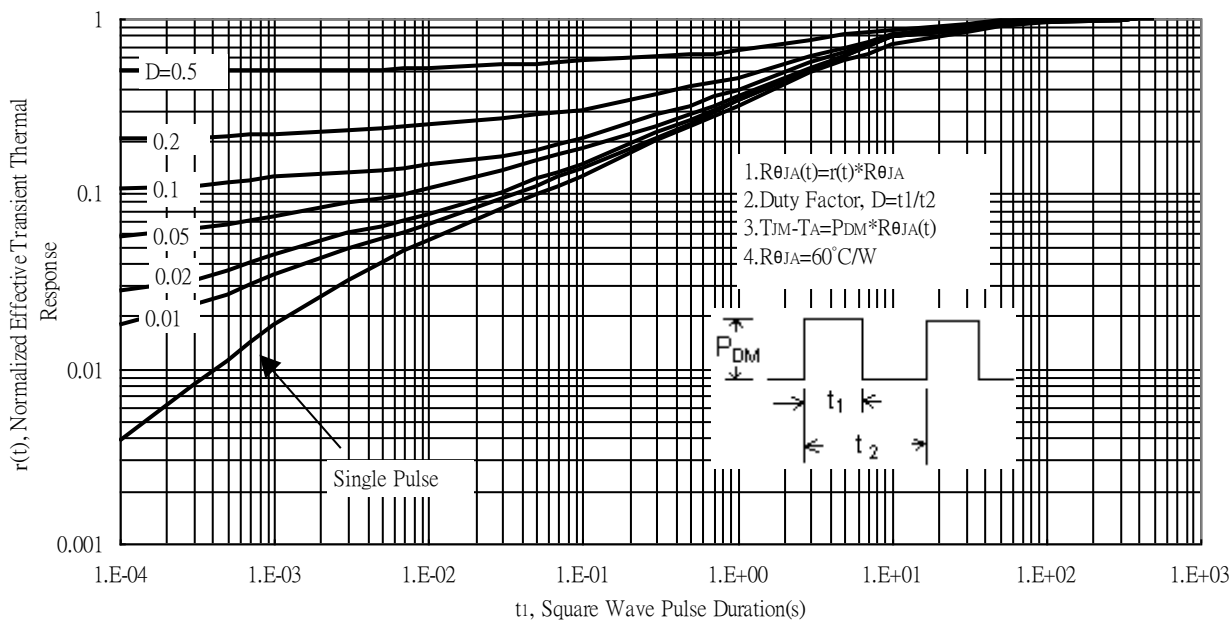
Typical Transfer Characteristics



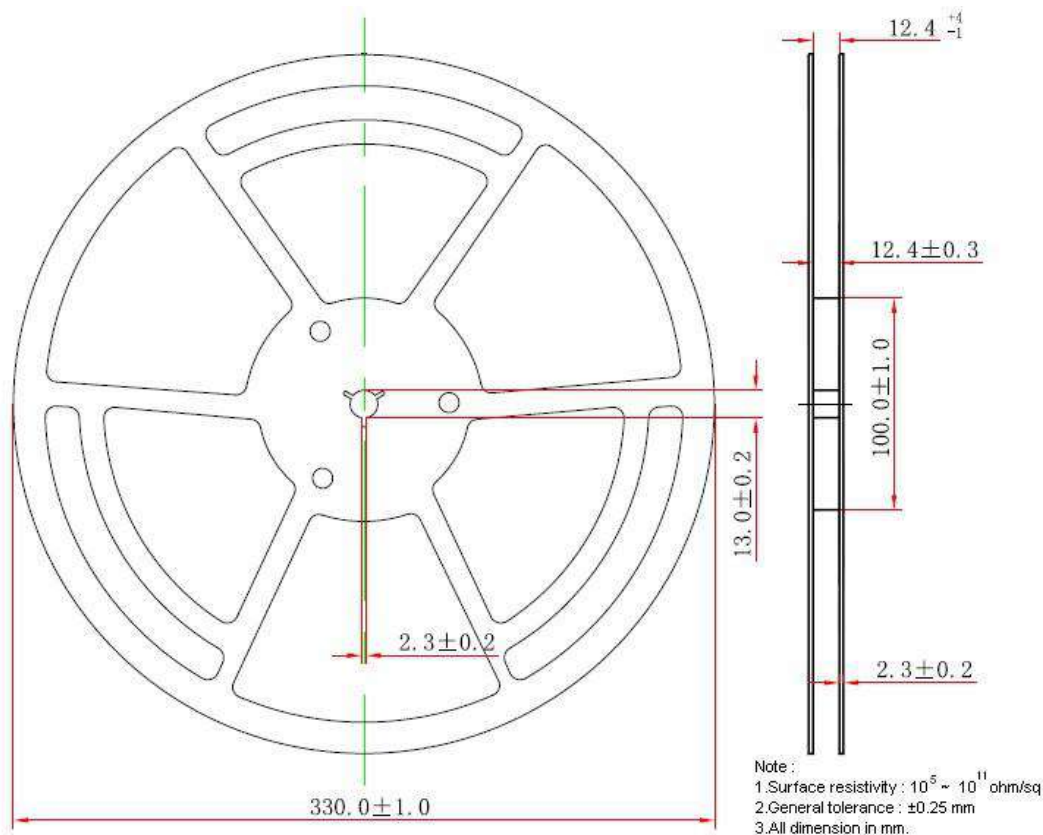
Single Pulse Maximum Power Dissipation



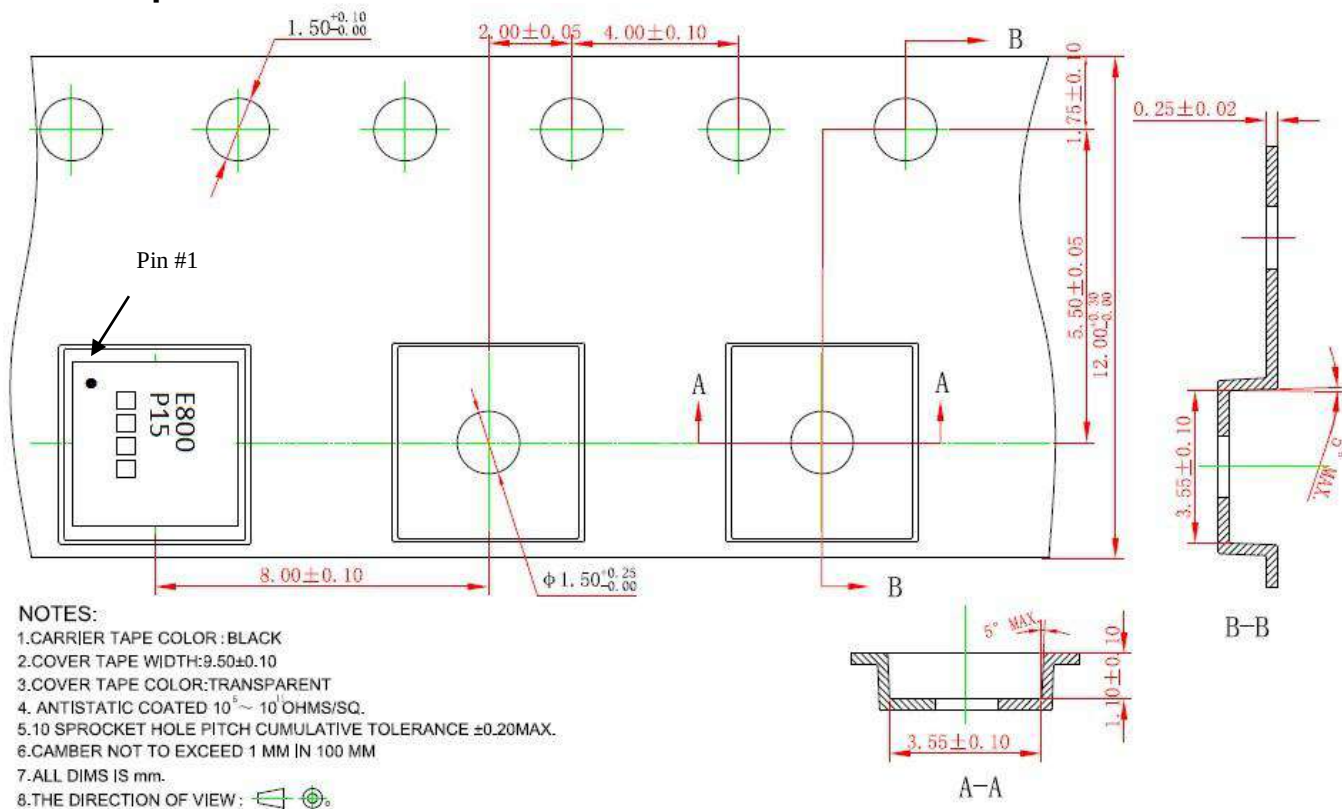
Transient Thermal Response Curves



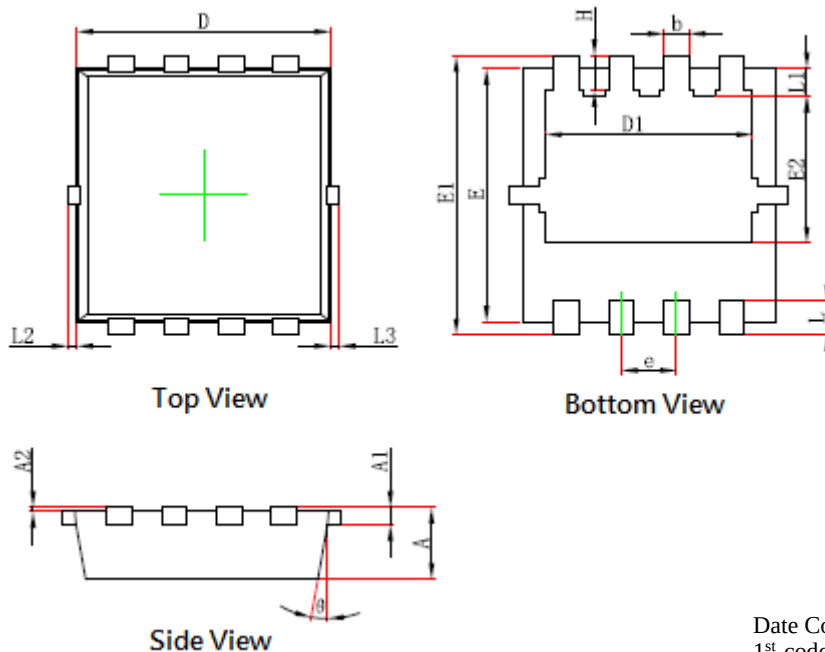
Reel Dimension



Carrier Tape Dimension

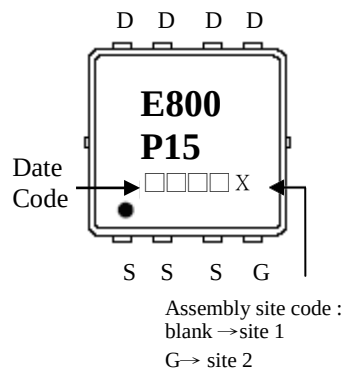


DFN3×3 Dimension



8-Lead DFN3×3 Plastic Package

Marking:



Date Code(counting from left to right) :

1st code: year code, the last digit of Christian year

2nd code : month code, Jan→A, Feb→B, Mar→C, Apr→D

May→E, Jun→F, Jul→G, Aug→H, Sep→J,

Oct→K, Nov→L, Dec→M

3rd and 4th codes : production serial number, 01~99

DIM	Inches		Millimeters		DIM	Inches		Millimeters	
	Min.	Max.	Min.	Max.		Min.	Max.	Min.	Max.
A	0.026	0.033	0.650	0.850	b	0.008	0.016	0.200	0.400
A1	0.006	REF	0.152	REF	e	0.022	0.030	0.550	0.750
A2	0.000	0.002	0.000	0.050	L	0.012	0.020	0.300	0.500
D	0.114	0.126	2.900	3.200	L1	0.007	0.019	0.180	0.480
D1	0.091	0.102	2.300	2.600	L2	0.000	0.006	0.000	0.150
E	0.114	0.126	2.900	3.200	L3	0.000	0.006	0.000	0.150
E1	0.124	0.136	3.150	3.450	H	0.012	0.020	0.300	0.515
E2	0.058	0.076	1.480	1.935	θ	8°	13°	8°	13°